Docket No. 239525US2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yukio TANIGUCHI, et al.

SERIAL NO: New Application GAU:

FILED: Herewith EXAMINER:

FOR: CRYSTALLIZATION APPARATUS, OPTICAL MEMBER FOR USE IN CRYSTALLIZATION APPARATUS, CRYSTALLIZATION METHOD, THIN FILM TRANSISTOR, AND DISPLAY

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

■ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.

☐ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.

☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.

☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

■ Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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STATEMENT OF RELEVANCY

Reference AV and AW of Form PTO-1449:

This documents are disclosed in the body of the specification.

Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO.	SERIAL NO.
		239525US2	New Application
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT	
		Yukio TANIGUCHI, et al.	
		FILING DATE	GROUP
		Herewith	

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	TRANSLATION NO
	AO					
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AV	Masakiyo MATSUMURA, "PREPARATION OF ULTRA-LARGE GRAIN SILICON THIN-FILMS BY EXCIMER-LASER", Surface Science, Vol. 21, No. 5, pp. 278-287, 2000.
	AW	2000-306859, published November 2, 2000.
	AX	M. NAKATA, et al., "TWO-DIMENSIONALLY POSITION-CONTROLLED ULTRA-LARGE GRAIN GROWTH BASED ON PHASE-MODULATED EXCIMER-LASER ANNEALING METHOD", Department of Physical Electronics, Tokyo Institute of Technology, Electrochemical Society Proceedings, Vol. 2000-31, pgs. 148 – 154.
	AY	Wen-Chang YEH, et al., "EFFECTS OF A LOW-MELTING-POINT UNDERLAYER ON EXCIMER-LASER-INDUCED LATERAL CRYSTALLIZATION OF Si THIN-FILMS", Jpn. J. Appl. Phys. Vol. 40 (2001), Part 1,No. 5A, May 2001, pp. 3096 - 3100
	AZ	Y. SANO, et al., "HIGHLY PACKED AND ULTRA-LARGE Si GRAINS GROWN BY A SINGLE-SHOT IRRADIATION OF EXCIMER-LASER LIGHT PULSE", Department of Physical Electronics, Tokyo Institute of Technology, (8 pages)

☐ *Additional References sheet(s) attached*

Examiner	Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.